

MARKED-UP COPY OF AMENDMENTS TO THE CLAIMS

35. (Amended) A method of fabricating a semiconductor structure, the method comprising the steps of:

providing a semiconductor substrate; and

providing ~~at least one lattice mismatched epitaxial layer on said substrate~~ a graded region incorporating compressive strain to offset tensile strain arising during processing;

and

~~planarizing the surface of said layer.~~

39. (Amended) The method of claim ~~38~~35, wherein ~~said the graded region~~ comprises Si and Ge graded to an increasing concentration of Ge, and the step of incorporating compressive strain comprises decreasing ~~the growth~~ a temperature at which the graded region is grown as the Ge concentration increases in said graded region.

42. (Amended) The method of claim 35, wherein said ~~layer~~region is partially relaxed.

43. (Amended) The method of claim 35, wherein said ~~layer~~region is fully relaxed.